1N60 THRU 1N60P
SMALLE SIGNAL SCHOTTKY RECTIFIERS

FEATURES:

- Metal-on-silicon junction,majority camier conduction
- High currentcapability,low forward voltage drop
- Ultra speed switching characteristics
- Extremely low reverse current IR
- Satisfactory wave detecion efficiency
- Small temperature coefficien of forward characterisits
- For use in Recorder/TV/RADIO/TELEPHONE as detectors,high speed switching circuits,small current rectifier

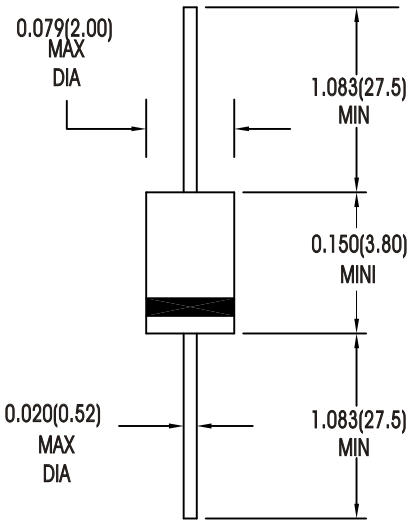
MECHANICAL DATA

Case: DO-35 glass case

Polarity: color band denotes cathode end

Weight:Approx 0.13 grams

DO-35



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25° C ambient temp. unless otherwise specified.

Single phase, half sine wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20 %.

Characteristic	Symbol	1N60	1N60P	Units
Repetitive peak reverse voltage	V_{RRM}	20	30	Volts
Forward currentt at Ta=25℃	I_O	30	50	mA
Peak forward surge current,t=1S	I_{FSM}	150	400	mA
Maximum instantaneous forward voltage drop at IF=1.0mA	V_F	0.50	0.50	Volts
Maximum instantaneous forward voltage drop at IF=30mA	V_F	1.0		Volts
Maximum instantaneous forward voltage drop at IF=200mA	V_F		1.0	Volts
Maximum reverse current At VR=15V 25°C	I_R	5.0	10	μA
Typical junction capacitance (Note 1)	C_F	4.0	10	PF
Typical Efficiency(See diagram 4) (Note 2)	η	60		%
Maximum reverse Recovery time (Note 3)	T_{RR}	1.0		ns
Typical Junction Ambient Themal Resistance	$R_{\theta JT}$	400		°C/W
Operating temperature range	T_J	-65 to+125		°C
Storage temperature range	Tstg	-65 to+125		°C

Nonte : 1. VR=1V ,f=1MHZ For 1N60,VR=10V ,f=1MHZ For 1N60P

2. V_I =3V, f=300MHZ ,C_L=10P$_F$,R_L =3.8KΩ

3.I =I =1mA, Trr=1mA, Rc=100Ω

FIG.1-FORWARD CURRENT

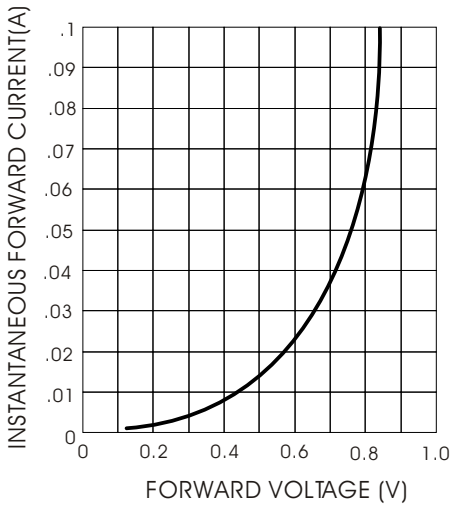


FIG.2-REVERSE CURRENT

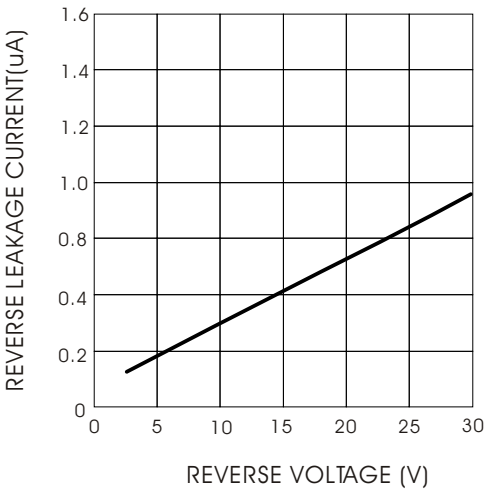


FIG.3-JUNCTION CAPACITANCE

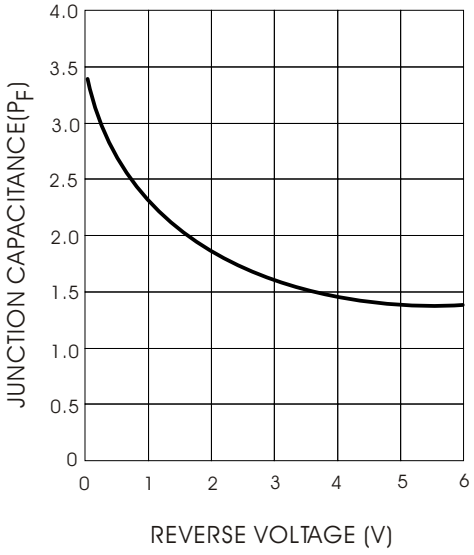
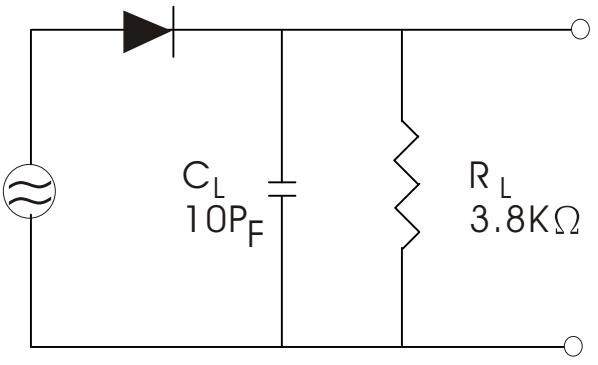


FIG.4-DETECTION EFFICIENCY MEEASUREMENT CIRCUIT



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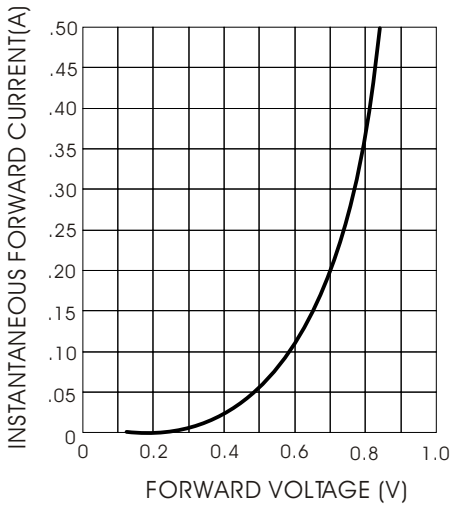
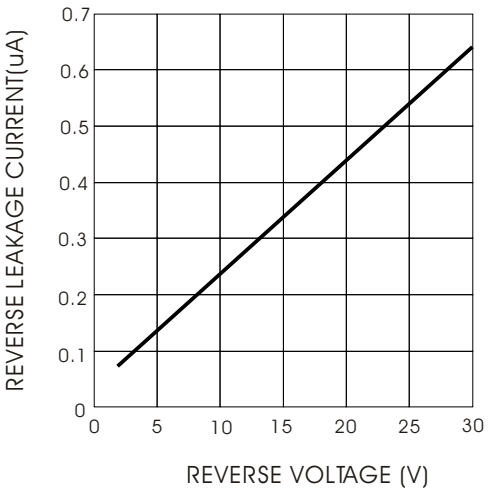


FIG.2-REVERSE CURRENT



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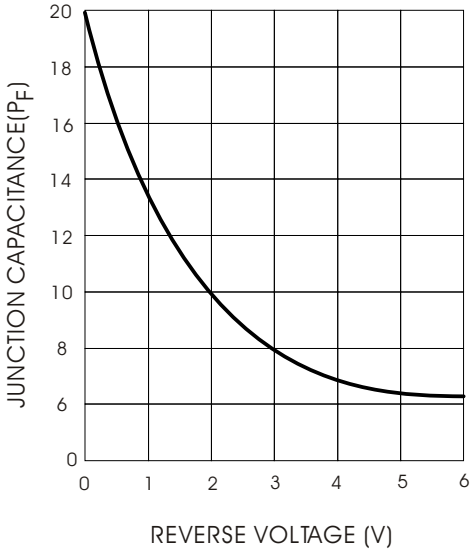

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